Fri, 23 Jun 2006, 4:04:12 PM EST

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#1	((wafer <near> fabrication and track and scanner) <in>metadata)	0
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#3	((wafer and fabrication)<in>metadata)	2550
#4	((((wafer and fabrication)<in>metadata))<AND>(track and scan*<in>metadata))	7
#5	((((((wafer and fabrication)<in>metadata))<and>(track and scan*<in>metadata)))<AND>(wait <near> states<in>metadata))	0
#6	((((((wafer and fabrication)<in>metadata))<and>(track and scan*<in>metadata)))<and>(pre-planned or planned<in>metadata))	1

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IEEE JNL	IEEE Journal or Magazine
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1. **A new solenoid magnetic integrated head for digital video recording**
Albertini, J.-B.; Sibuet, H.; Renaux, P.; Gaud, P.;
Magnetics, IEEE Transactions on
Volume 33, Issue 5, Part 1, Sept. 1997 Page(s):2836 - 2838
Digital Object Identifier 10.1109/20.617748
AbstractPlus | References | Full Text: PDF(700 KB) **IEEE JNL**
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2. **Yield enhancement in photolithography through model-based process control: average mode control**
Grosman, B.; Lachman-Shalem, S.; Swissa, R.; Lewin, D.R.;
Semiconductor Manufacturing, IEEE Transactions on
Volume 18, Issue 1, Feb 2005 Page(s):86 - 93
Digital Object Identifier 10.1109/TSM.2004.836654
AbstractPlus | Full Text: PDF(488 KB) **IEEE JNL**
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3. **Photoluminescence and photoreflectance scanning of silicon-on-insulator materials**
Hovel, H.J.;
SOI Conference, 1993. Proceedings., 1993 IEEE International
5-7 Oct. 1993 Page(s):26 - 27
Digital Object Identifier 10.1109/SOI.1993.344607
AbstractPlus | Full Text: PDF(248 KB) **IEEE CNF**
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4. **Defect inspection sampling plans-which one is right for me?**
Scanlan, B.;
Advanced Semiconductor Manufacturing Conference and Workshop, 1998. 1998 IEEE/SEMI
23-25 Sept. 1998 Page(s):103 - 108
Digital Object Identifier 10.1109/ASMC.1998.731415
AbstractPlus | Full Text: PDF(660 KB) **IEEE CNF**
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5. **Surface micromachined polyimide scanning thermocouple probes**
Li, M.-H.; Wu, J.J.; Gianchandani, Y.B.;
Microelectromechanical Systems, Journal of
Volume 10, Issue 1, March 2001 Page(s):3 - 9
Digital Object Identifier 10.1109/84.911085
AbstractPlus | References | Full Text: PDF(164 KB) **IEEE JNL**
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☐ **6. Monolithically cascaded micromirror pair driven by angular vertical combs for two-axis scanning**
Fujino, M.; Patterson, P.R.; Nguyen, H.; Piyawattanametha, W.; Wu, M.C.;
Selected Topics in Quantum Electronics, IEEE Journal of
Volume 10, Issue 3, May-June 2004 Page(s):492 - 497
Digital Object Identifier 10.1109/JSTQE.2004.829203
AbstractPlus | References | Full Text: PDF(320 KB) **IEEE JNL**
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☐ **7. Feature-scale Process Simulation and accurate capacitance extraction for the backend of a 100-nm aluminum/TEOS Process**
Heitzinger, C.; Sheikholeslami, A.; Badrieh, F.; Puchner, H.; Selberherr, S.;
Electron Devices, IEEE Transactions on
Volume 51, Issue 7, July 2004 Page(s):1129 - 1134
Digital Object Identifier 10.1109/TED.2004.829868
AbstractPlus | References | Full Text: PDF(488 KB) **IEEE JNL**
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IEEE STD	IEEE Standard

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1. **Defect inspection sampling plans-which one is right for me?**
Scanlan, B.;
Advanced Semiconductor Manufacturing Conference and Workshop, 1998. 1998 IEEE/SEMI
23-25 Sept. 1998 Page(s):103 - 108
Digital Object Identifier 10.1109/ASMC.1998.731415
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EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1	(semiconductor adj wafer near5 fabrication and track$3 and scanner and deviation and (planned pre-planned) near2 wait adj state$1 and avoid near conflict and compensat$3 and dynamically near2 insert$3 and time near delay)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/06/23 14:25
L2	1	(semiconductor adj wafer near5 fabrication and track$3 and scanner and deviation and (planned pre-planned) near2 wait adj state$1 and avoid near conflict and compensat$3 and dynamically near2 insert$3 and time near delay).clm.	US-PGPUB	OR	ON	2006/06/23 14:25
L3	13	("5455894" "2003045131" "6707545" "6308107" "2003099112").pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/06/23 14:26
L4	11	("5455894" "20030045131" "6707545" "6308107" "2003099112").pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/06/23 14:26
L5	0	L4 and clock with signal$1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/06/23 14:26
L6	0	L4 and clock	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/06/23 14:26
L7	7	L4 and signal$1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/06/23 14:26
L8	2	L4 and timer$1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/06/23 14:26

EAST Search History

L9	4548	(700/121,204,112,99,247,258,259, 254 414/937,940).ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/06/23 14:26
L10	738	L9 and (semiconductor wafer) with (fabricat$3) and (inspect$3 monitor$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/06/23 14:26
L11	129	L9 and (semiconductor wafer) with (fabricat$3) with (inspect$3 monitor$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/06/23 14:26
L12	3	L9 and (semiconductor wafer) with (fabricat$3) with (inspect$3 monitor$3) and clock near signal$1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/06/23 14:26
L13	0	L9 and (semiconductor wafer) with (fabricat$3) with (inspect$3 monitor$3) and clock near system	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/06/23 14:26
L14	18	L9 and (semiconductor wafer) with (fabricat$3) and (inspect$3 monitor$3) and (scanner$1 camera$1) and clock$1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/06/23 14:26
L15	7	L9 and (semiconductor wafer) with (fabricat$3) and (inspect$3 monitor$3) and (scanner$1 camera$1) and (deviation variation) with (adjustment compensation)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/06/23 14:26
L16	372	(semiconductor wafer) with (fabricat$3) and (inspect$3 monitor$3) and (scanner$1 camera$1) and (deviation variation) with (adjustment compensation)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/06/23 14:26
L17	0	(semiconductor wafer) with (fabricat$3) and (inspect$3 monitor$3) and (scanner$1 camera$1) and (clock time) with delay with (deviation variation) with (adjustment compensation)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/06/23 14:26

EAST Search History

L18	17	(semiconductor wafer) with (fabricat$3) and (inspect$3 monitor$3) and (scanner$1 camera$1) and (clock time) with (deviation variation) with (adjustment compensation)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/06/23 14:26
L19	25	oh near hilario.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/06/23 14:26
L28	1	(semiconductor and fabrication).ab. and (scanner$1 camera) with system adj clock	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/06/23 14:26
L29	0	(semiconductor and fabrication).ab. and (scanner$1 camera) with operating with (clock pulse$1) near signal$1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/06/23 14:26
L30	0	(semiconductor and fabrication).ab. and (scanner$1 camera) and operating with (clock pulse$1) near signal$1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/06/23 14:26
L31	1	(semiconductor and fabrication).ab. and (scan$$5 camera$1) and operating with (clock pulse$1) near signal$1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/06/23 14:26
L32	9	(semiconductor and fabrication).ab. and (scan$$5 camera$1) and operat$3 with (clock pulse$1) near signal$1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/06/23 14:26
L33	99	(semiconductor and fabrication).ab. and (scan$$5 camera$1) near system	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/06/23 14:26
L34	9	(semiconductor and fabrication).ab. and (scan$$5 camera$1) near system and (clock pulse$1) near signal$1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/06/23 14:26
L35	1	2004-699555.NRAN.	DERWENT	OR	ON	2006/06/23 14:26

EAST Search History

L36	8	(semiconductor and fabrication).ab. and (scan$$5) near system and (track$3 near system)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/06/23 14:26
L37	903	(semiconductor and fabrication).ab. and inspect$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/06/23 14:26
L38	61	(semiconductor and fabrication).ab. and inspect$3 and time adj delay$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/06/23 14:26
L39	42	(semiconductor and fabrication and inspect$3).ab. and time adj delay$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/06/23 14:26
L40	42	(semiconductor and fabrication and inspect$3).ab. and time adj delay$3 and (scan$5 camera$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/06/23 14:26
L41	2	(semiconductor and fabrication and inspect$3).ab. and time adj delay$3 and (scan$5 camera$1) and time near (calculation computation computing)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/06/23 14:26
L42	0	(semiconductor and fabrication and inspect$3).ab. and time adj delay$3 with (calculation computation computing) and (scan$5 camera$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/06/23 14:26
L43	0	(semiconductor and fabrication and inspect$3).ab. and time adj delay$3 same (calculation computation computing) and (scan$5 camera$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/06/23 14:26
L44	7	(semiconductor and fabrication and inspect$3).ab. and time same (calculation computation computing) and (scan$5 camera$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/06/23 14:26
L45	571	(semiconductor and fabrication and inspect$3) and time with (calculation computation computing) and (scan$5 camera$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/06/23 14:26

EAST Search History

L46	4	(semiconductor and fabrication and inspect$3) and time with (calculation computation computing) same (scan$5) with operat$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/06/23 14:26
L47	1692	(semiconductor and fabrication and inspect$3) and scanner	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/06/23 14:26
L48	5	(semiconductor and fabrication and inspect$3 and scanner).ab.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/06/23 14:26
L49	1773	(semiconductor and fabrication and inspect$3).ab. operating near scanner$1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/06/23 14:26
L50	452	(semiconductor and fabrication and inspect$3).ab. operating near scanner$1 with (clock pulse) near signal$1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/06/23 14:26
L51	448	(semiconductor and fabrication and inspect$3).ab. operating near scanner$1 with response with (clock pulse) near signal$1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/06/23 14:26
L52	0	(semiconductor and fabrication and inspect$3).ab. and operating near scanner$1 with response with (clock pulse) near signal$1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/06/23 14:26
L53	0	(semiconductor and fabrication and inspect$3).ab. and operating near scanner$1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/06/23 14:26
L54	4	semiconductor and fabrication and inspect$3 and operating near scanner$1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/06/23 14:26
L55	0	(wafer$1 and inspect$3).ab. and operating near scanner$1 with response with (clock pulse) near signal$1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/06/23 14:26

EAST Search History

L56	0	(wafer$1 and inspect$3).ab. and operating near scanner$1 with (clock pulse) near signal$1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/06/23 14:26
L57	0	(wafer$1 and inspect$3).ab. and operating near scanner$1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/06/23 14:26
L58	0	(wafer$1 and monitor$3).ab. and operating near scanner$1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/06/23 14:26
L59	0	(semiconductor and monitor$3).ab. and operating near scanner$1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/06/23 14:26
L60	0	(semiconductor and inspect$3).ab. and operating near scanner$1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/06/23 14:26
L61	11	(semiconductor and inspect$3).ab. and scanner$1 near system	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/06/23 14:26
L62	209	(semiconductor and inspect$3).ab. and time near delay$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/06/23 14:26
L63	9	(semiconductor and inspect$3).ab. and time near delay$3 and time near (calculation calculating calculated computing computation calculates computes computed)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/06/23 14:26
L64	0	(semiconductor and inspect$3).ab. and scan$4 near delay$3 and time near (calculation calculating calculated computing computation calculates computes computed)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/06/23 14:26
L65	9	semiconductor and inspect$3 and scan$4 near delay$3 and time near (calculation calculating calculated computing computation calculates computes computed)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/06/23 14:26

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L71	33	semiconductor and inspection near scanner	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/06/23 14:26
L72	0	semiconductor and inspection near scanner and number adj of adj wafer$1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/06/23 14:26
L73	2	semiconductor and inspection near scanner and wafer$1 with count$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/06/23 14:26
L76	615	wafer adj per adj hour	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/06/23 14:26
L77	615	wafers adj per adj hour	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/06/23 14:26
L78	2	(moving carrying transporting) near5 (wafer$ adj per adj hour)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/06/23 14:26
L79	0	(moving carrying transporting) near5 (wafer$ near hour)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/06/23 14:26
L80	0	(moving carrying transporting conveying) near5 (wafer$ near hour)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/06/23 14:26
L81	6	(moving carrying transporting conveying) near5 (wafer$ near3 hour)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/06/23 14:26
L82	0	(semiconductor with fabrication) and process$3 with speed and (number adj of amount adj of) near5 wafers	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/06/23 14:26

EAST Search History

L83	0	(semiconductor with fabrication) and process$3 with speed and (number adj of amount adj of) with wafers	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/06/23 14:26
L84	0	(semiconductor with fabrication) and scan$4 and (number adj of amount adj of) with wafers	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/06/23 14:26
L85	0	(semiconductor with fabrication) and scan$4 and (number adj of amount adj of) adj wafers	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/06/23 14:26
L86	10331	(semiconductor with fabrication) and scan$4 and wafers	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/06/23 14:26
L87	2500	(semiconductor with fabrication) and scan$4 and (number amount) near5 wafers	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/06/23 14:26
L88	0	(semiconductor with fabrication) and scan$4 and (number amount) adj of near5 wafers	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/06/23 14:26
L89	1064	(semiconductor with fabrication) and scan$4 and (number amount) near3 wafers and speed	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/06/23 14:26
L90	207	(semiconductor with fabrication) and scan$4 and (number amount) near3 wafers and scan$4 near3 speed	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/06/23 14:26
L91	22	(semiconductor with fabrication) and scan$4 with (number amount) near3 wafers and scan$4 near3 speed	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/06/23 14:26
L92	68	(semiconductor with fabrication) and scan$4 with (number amount) near3 wafers and throughput	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/06/23 14:26

EAST Search History

L96	3146	(700/121,99,112,204,247,254,258, 259).ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/06/23 15:33
L97	1442	414/937;940.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/06/23 15:33